











SN74LVTH16373-EP

SCBS778B - NOVEMBER 2003 - REVISED JUNE 2016

SN74LVTH16373-EP 3.3-V ABT 16-Bit Transparent D-Type Latch With Tri-State Outputs

Features

- Controlled Baseline
 - One Assembly/Test Site, One Fabrication Site
- **Enhanced Diminishing Manufacturing Sources** (DMS) Support
- **Enhanced Product-Change Notification**
- Qualification Pedigree (1)
- Member of the Texas Instruments Widebus™ Family
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Supports Unregulated Battery Operation Down to
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Ioff and Power-Up Tri-State Support Hot Insertion
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds JESD 22
 - 4000-V Human Body Model (A114-A)
 - 200-V Machine Model (A115-A)

Applications

- Data Buffer
- **Bus Driver**
- Display Driver

Description

The SN74LVTH16373 is a 16-bit transparent D-type latch with tri-state outputs designed for low-voltage (3.3 V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. This device can be used as two 8-bit latches or one 16-bit latch. When the latchenable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

Device Information⁽²⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
SN74LVTH16373-EP	TSSOP (48)	12.50 mm × 6.10 mm	
	SSOP (48)	15.88 mm × 7.49 mm	
	BGA MICROSTAR JUNIOR (56)	4.50 mm × 7.00 mm	

- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave unbiased or electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond performance and environmental limits.
- (2) For all available packages, see the orderable addendum at the end of the data sheet.

SN74LVTH16373-EP Single Channel Block Diagram

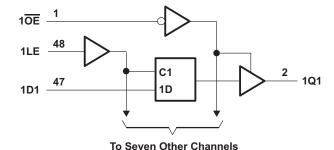




Table of Contents

1	Features 1		8.1 Overview	12
2	Applications 1		8.2 Functional Block Diagram	12
3	Description 1		8.3 Feature Description	12
4	Revision History2		8.4 Device Functional Modes	12
5	Pin Configuration and Functions	9	Application and Implementation	13
6	Specifications4		9.1 Application Information	13
٠	6.1 Absolute Maximum Ratings		9.2 Typical Application	13
	6.2 ESD Ratings	10	Power Supply Recommendations	15
	6.3 Recommended Operating Conditions	11	Layout	15
	6.4 Thermal Information		11.1 Layout Guidelines	15
	6.5 Electrical Characteristics 6		11.2 Layout Example	15
	6.6 Timing Requirements (I Version)	12	Provice and Documentation Support	16
	6.7 Switching Characteristics (I Version)		12.1 Receiving Notification of Documentation Updates	16
	6.8 Timing Requirements (M Version)		12.2 Community Resources	16
	6.9 Switching Characteristics (M Version)		12.3 Trademarks	16
	6.10 Typical Characteristics		12.4 Electrostatic Discharge Caution	16
7	Parameter Measurement Information		12.5 Glossary	
8	Detailed Description	13	Mechanical, Packaging, and Orderable Information	

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

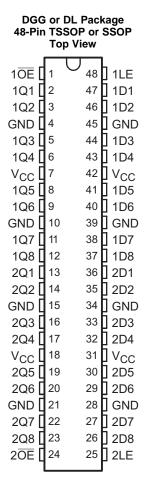
Changes from Revision A (March 2004) to Revision B

Page

•	Added Pin Functions table, ESD Ratings table, Thermal Information table, Typical Characteristics section, Detailed Description section, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section
•	Corrected table notes for Absolute Maximum Ratings table
•	Added new device temperature range to Recommended Operating Conditions table
•	Added new device specifications in Timing Requirements (M Version) and Switching Characteristics (M Version) tables 8
•	Added Figure 1 to Specifications section



5 Pin Configuration and Functions



GQL Package 56-Pin BGA MICROSTAR JUNIOR Top View 2 3 4 5 6 000000 Α 000000 В 000000 С 000000 D \bigcirc \bigcirc Ε 0000F 000000 G 000000 н 000000 J 000000 K

Table 1. Pin Assignments⁽¹⁾

	1	2	3	4	5	6
Α	1 OE	NC	NC	NC	NC	1LE
В	1Q2	1Q1	GND	GND	1D1	1D2
С	1Q4	1Q3	VCC	VCC	1D3	1D4
D	1Q6	1Q5	GND	GND	1D5	1D6
Е	1Q8	1Q7			1D7	1D8
F	2Q1	2Q2			2D2	2D1
G	2Q3	2Q4	GND	GND	2D4	2D3
Н	2Q5	2Q6	VCC	VCC	2D6	2D5
J	2Q7	2Q8	GND	GND	2D8	2D7
K	2 OE	NC	NC	NC	NC	2LE

(1) NC - No internal connection.



Pin Functions

	PIN	1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
1Dn ⁽¹⁾	37, 38, 49, 41, 43, 44, 46, 47	1	Data input pins
1LE	48	1	Latch enable pin to control 1Qn output states
1 OE	1	1	Active low enable pin for 1Qn pins
1Qn ⁽¹⁾	2, 3, 5, 6, 8, 9, 11, 12	0	Output pins
2Dn ⁽¹⁾	26, 27, 29, 30, 32, 33, 35, 36	1	Data input pins
2LE	25	1	Latch enable pin to control 2Qn output states
2Qn ⁽¹⁾	13, 14, 16, 17, 19, 20, 22, 23	0	Output pins
2 OE	24	1	Active low enable pin for 2Qn pins
GND	4, 10, 15, 21, 28, 34, 39, 45	_	Ground
VCC	7, 18, 31, 42	1	Power supply input for internal circuits

^{(1) &}quot;n" denotes numbering (1 to 8) for data input and output pins.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	4.6	V
VI	Input voltage ⁽²⁾	-0.5	7	V
Vo	Voltage applied to any output in the high-impedance or power-off state (2)	-0.5	7	V
Vo	Voltage applied to any output in the high state ⁽²⁾	-0.5	V _{CC} + 0.5 V	V
Io	Current into any output in the low state		128	mA
Io	Current into any output in the high state (3)		64	mA
I _{IK}	Input clamp current (V _I < 0)	-50		mA
I _{OK}	Output clamp current (V _O < 0)	-50		mA
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per A114-A	±4000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽¹⁾	±3000	V
		Machine model (MM), per A115-A	200	V

(1) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽³⁾ This current flows only when the output is in the high state and $V_O > V_{CC}$.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2.7	3.6	V
V _{IH}	High-level input voltage		2		V
V _{IL}	Low-level input voltage			0.8	V
VI	Input voltage			5.5	V
I _{OH}	High-level output current			-32	mA
I _{OL}	Low-level output current			64	mA
Δt/Δν	Input transition rise or fall rate, outputs ena	bled		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		μs/V
T _A	Operating ambient temperature	I version	-40	85	°C
		M version	-55	125	°C

⁽¹⁾ All unused control inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.4 Thermal Information

			SN74LVTH1	6373-EP	
	THERMAL METRIC(1)(2)	DGG (TSSOP)	DL (SSOP)	GQL (BGA MICROSTAR JUNIOR)	UNIT
		48 PINS	48 PINS	56 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	68.9	60.3	62.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	14.6	31	24.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	35.8	32.1	28.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	2.4	9.3	0.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	35.5	31.8	28	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

⁽²⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted); all typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER		TEST CONI	DITIONS	MIN	TYP	MAX	UNIT
V _{IK}		V _{CC} = 2.7 V,	I _I = -18 mA			-1.2	V
		V _{CC} = 2.7 V to 3.6 V,	I _{OH} = -100 μA	V _{CC} - 0.2			V
V _{OH}		V _{CC} = 2.7 V,	I _{OH} = -8 mA	2.4			V
		V _{CC} = 3 V,	I _{OH} = -32 mA	2			V
		V _{CC} = 2.7 V	I _{OL} = 100 μA			0.2	V
		V _{CC} = 2.7 V	I _{OL} = 24 mA			0.5	V
V_{OL}			I _{OL} = 16 mA			0.4	V
		$V_{CC} = 3 V$,	$I_{OL} = 32 \text{ mA}$			0.5	V
			$I_{OL} = 64 \text{ mA}$			0.55	V
		$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	$V_1 = 5.5 \text{ V}$			10	μΑ
	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND			±1	μΑ
l _l	Data innuta	V - 26 V	$V_I = V_{CC}$			1	μΑ
	Data inputs	$V_{CC} = 3.6 \text{ V}$	$V_I = 0$			-5	μΑ
I _{off}		$V_{CC} = 0$,	V_I or $V_O = 0$ to 4.5 V			±100	μΑ
	Data inputs	V _{CC} = 3 V	$V_{I} = 0.8 \text{ V}$	75			μΑ
I _{I(hold)}			V _I = 2 V	-75			μΑ
		$V_{CC} = 3.6 V^{(1)},$	$V_{I} = 0 \text{ to } 3.6 \text{ V}$			±650	μΑ
l _{OZH}		V _{CC} = 3.6 V,	V _O = 3 V			5	μΑ
l _{OZL}		$V_{CC} = 3.6 \text{ V},$	V _O = 0.5 V			- 5	μΑ
I _{OZPU}		$V_{CC} = 0$ to 1.5 V, $V_{O} = 0.5$ to 3	V, OE = don't care			±100	μΑ
I _{OZPD}		$V_{CC} = 1.5 \text{ V to } 0, V_{O} = 0.5 \text{ to } 3$	V, OE = don't care			±100	μΑ
			Outputs high			0.19	mA
I _{CC}		$V_{CC} = 3.6 \text{ V}, I_{O} = 0, V_{I} = V_{CC}$ or GND	Outputs low			5	mA
		0.0.15	Outputs disabled			0.19	mA
ΔI _{CC} ⁽²⁾		V _{CC} = 3 to 3.6 V, One input at at V _{CC} or GND	V _{CC} - 0.6 V, Other inputs			0.2	mA
Ci		V _I = 3 V or 0			3		pF
Co		V _O = 3 V or 0			9		pF

⁽¹⁾ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

(2) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

Submit Documentation Feedback

Copyright © 2003–2016, Texas Instruments Incorporated



6.6 Timing Requirements (I Version)

over recommended operating conditions (unless otherwise noted); $T_A = -40$ °C to 85°C

			MIN N	IAX UNIT
	$V_{CC} = 2.7 \text{ V}$	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	3	ns
'w		V _{CC} = 2.7 V	3	ns
	Cotton time data before LEI	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1	ns
l _{su}	Setup time, data before LE↓	$V_{CC} = 2.7 \text{ V}$	3 3 1 0.6 1	ns
	Hold time, data after LE↓	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1	ns
t _h		V _{CC} = 2.7 V	1.1	ns

6.7 Switching Characteristics (I Version)

over recommended operating conditions (unless otherwise noted); $T_A = -40^{\circ}C$ to 85°C; all typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
	-	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.7	3.8	ns		
t _{PLH}	D	Q	V _{CC} = 2.7 V			4.2	ns		
	D	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.5	3.6	ns		
t _{PHL}	D	Q	V _{CC} = 2.7 V			4	ns		
•	LE	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.1	3	4.3	ns		
t _{PLH}	LE	Q	V _{CC} = 2.7 V			4.8	ns		
	LE	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.1	2.9	4	ns		
t _{PHL}	LE	Q	V _{CC} = 2.7 V			4	ns		
	ŌĒ	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.8	4.3	ns		
t _{PZH}	OE	OE Q	V _{CC} = 2.7 V			5.1	ns		
			OE Q	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.8	4.3	ns
t _{PZL}	OE	Q	V _{CC} = 2.7 V			4.7	ns		
	ŌĒ	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.4	3.5	5	ns		
t _{PHZ}	OE	Q	V _{CC} = 2.7 V			5.4	ns		
t _{PLZ}	0 -	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2	3.2	4.7	ns		
	J OE	OE Q	V _{CC} = 2.7 V			4.8	ns		
t _{sk(o)}			V _{CC} = 3.3 V ± 0.3 V	0.5			ns		



6.8 Timing Requirements (M Version)

over recommended operating conditions (unless otherwise noted); $T_A = -55$ °C to 125°C

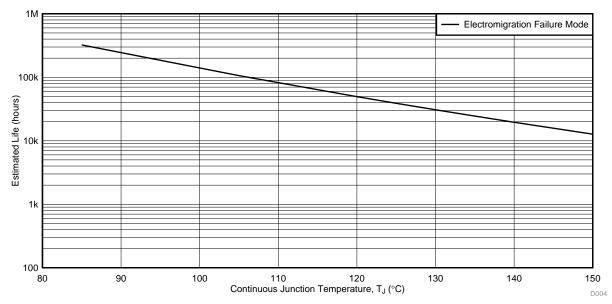
			MIN	MAX	UNIT
t _w	Pulse duration, LE high	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	3		ns
		V _{CC} = 2.7 V	3		ns
	Setup time, data before LE↓	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.6		ns
t _{su}		$V_{CC} = 2.7 \text{ V}$	1		ns
t _h	Hold time, data after LE↓	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.4		ns
		V _{CC} = 2.7 V	1.5		ns

6.9 Switching Characteristics (M Version)

over recommended operating conditions (unless otherwise noted); $T_A = -55^{\circ}C$ to 125°C; all typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	D	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.7	5	ns
t _{PLH}	Ь	Q	V _{CC} = 2.7 V			5.5	ns
	D	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.5	4.8	ns
t _{PHL}	D	Q	V _{CC} = 2.7 V			5.3	ns
t _{PLH}	1.5	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.1	3	5.4	ns
	LE	Q	V _{CC} = 2.7 V			5.9	ns
t _{PHL}	LE	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2.1	2.9	4.9	ns
		Q	V _{CC} = 2.7 V			4.9	ns
	ŌĒ	Q	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.8	7	ns
t _{PZH}		Q	V _{CC} = 2.7 V			7.9	ns
	ŌĒ	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.5	2.8	6.2	ns
t _{PZL}		Q	V _{CC} = 2.7 V			7.2	ns
	ŌĒ	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	1.8	3.5	7.2	ns
t _{PHZ}		Ē Q	V _{CC} = 2.7 V			7.9	ns
	ŌĒ Q	0	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	2	3.2	5.2	ns
t _{PLZ}		UE Q	V _{CC} = 2.7 V			5.4	ns
t _{sk(o)}			$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0.5			ns



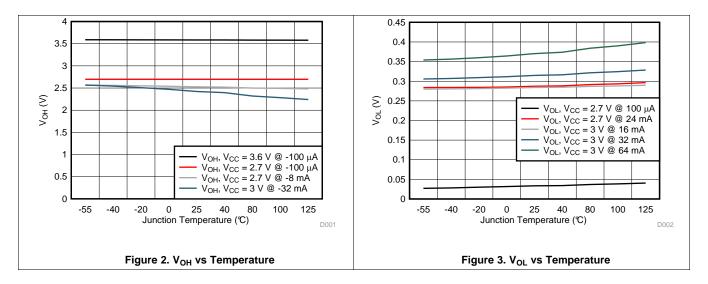


- (1) See data sheet for absolute maximum and minimum recommended operating conditions.
- (2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- (3) Enhanced plastic product disclaimer applies.

Figure 1. Derating Chart for SN74LVTH16373-EP

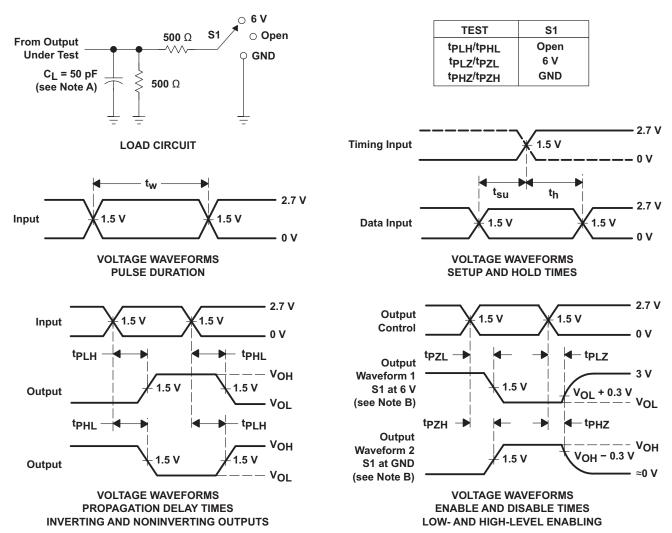


6.10 Typical Characteristics





7 Parameter Measurement Information



- A. CL includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time, with one transition per measurement.

Figure 4. Load Circuit and Voltage Waveforms



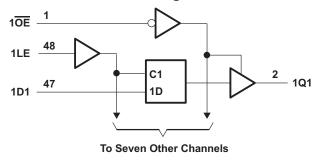
8 Detailed Description

8.1 Overview

The SN74LVTH16373 is a 16-bit transparent D-type latch with tri-state outputs designed for low-voltage (3.3-V) VCC operation, but with the capability to provide a TTL interface to a 5-V system environment. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. This device can be used as two 8-bit latches or one 16-bit latch. When the latchenable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable (OE) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components. OE does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

8.2 Functional Block Diagram



2DE 24

2LE 25

2D1 36

C1 13 2Q1

Figure 5. Logic Diagram (Positive Logic)

To Seven Other Channels
Figure 6. Logic Diagram (Positive Logic)

8.3 Feature Description

The SN74LVTH16373 included active bus-hold circuitry that holds unused or undriven inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended. Additionally, it features power up three state that will keep the outputs in high-impedance state during power up or power down when VCC is between 0 and 1.5 V. This prevents driver conflict during power up.

To ensure the high-impedance state above 1.5 V, OE should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for hot-insertion applications using I_{off} and power-up tri-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Table 2. Function Table (Each 8-Bit Section)

	OUTPUT					
ŌĒ	OE LE D					
L	Н	Н	Н			
L	Н	L	L			
L	L	X	Q_0			
Н	X	X	Z			

8.4 Device Functional Modes

Device functions as tristatable 8 or 16-bit latch per function table defined in Table 2.



Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The specially designed 3-V LVTH family uses the 0.8-µ BiCMOS process technology for bus-interface functions. Like its 5-V ABT counterpart, LVHT provides up to 64 mA of drive, low propagation delays. The bus-hold feature eliminates requirements for external pullup resistors and I/Os that can handle up to 7 V, which allows them to act as 5-V/3-V translators.

9.2 Typical Application

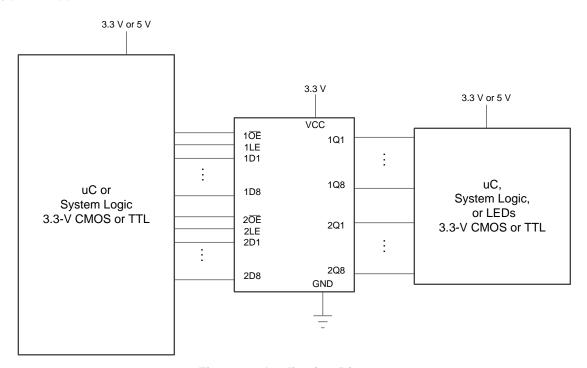


Figure 7. Application Diagram

9.2.1 Design Requirements

The SN54LVTH16373 utilizes BiCMOS technology with high-drive currents. Care must be taken to avoid bus contention that can disrupt system functionality and/or cause violation of absolute maximum ratings.

9.2.2 Detailed Design Procedure

- Recommended input conditions
 - Rise time and fall time specifications. See Δt/ΔV in Recommended Operating Conditions.
 - Specified high and low levels. See V_{IH} and V_{IL} in Recommended Operating Conditions.
 - Inputs are overvoltage tolerant, which allows them to go as high as 5.5 V independent of V_{CC}.
- Recommend output conditions
 - Avoid buss contention.

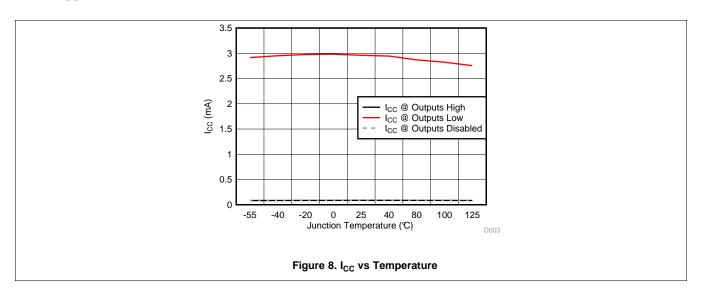
Copyright © 2003-2016, Texas Instruments Incorporated

- Do not exceed I_{OH} and I_{OL} current limits in Recommended Operating Conditions.
- Outputs that are being driven high may not be pulled above V_{CC} by more they 0.5 V.



Typical Application (continued)

9.2.3 Application Curves





10 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ F is recommended. If there are multiple V_{CC} pins, 0.01 μ F or 0.022 μ F is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 9 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

11.2 Layout Example

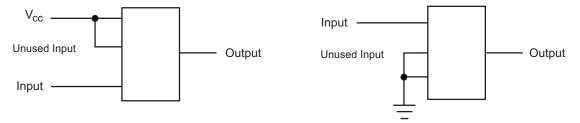


Figure 9. Layout Diagram

Product Folder Links: SN74LVTH16373-EP

Copyright © 2003-2016, Texas Instruments Incorporated



12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

Widebus, E2E are trademarks of Texas Instruments.

All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 10-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
CLVTH16373IDGGREP	Active	Production	TSSOP (DGG) 48	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH16373EP
CLVTH16373IDLREP	Active	Production	SSOP (DL) 48	1000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH16373EP
V62/04712-01XE	Active	Production	TSSOP (DGG) 48	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH16373EP
V62/04712-01YE	Active	Production	SSOP (DL) 48	1000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LH16373EP

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVTH16373-EP:

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

www.ti.com 10-Nov-2025

● Catalog : SN74LVTH16373

• Military : SN54LVTH16373

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

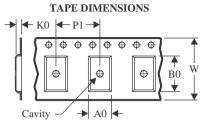
• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 24-Jul-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CLVTH16373IDGGREP	TSSOP	DGG	48	2000	330.0	24.4	8.6	13.0	1.8	12.0	24.0	Q1
CLVTH16373IDLREP	SSOP	DL	48	1000	330.0	32.4	11.35	16.2	3.1	16.0	32.0	Q1

www.ti.com 24-Jul-2025

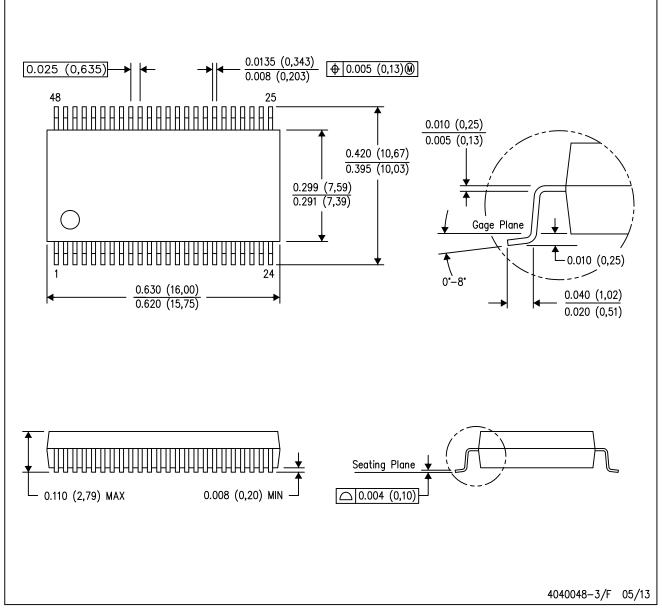


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CLVTH16373IDGGREP	TSSOP	DGG	48	2000	356.0	356.0	45.0
CLVTH16373IDLREP	SSOP	DL	48	1000	356.0	356.0	53.0

DL (R-PDSO-G48)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

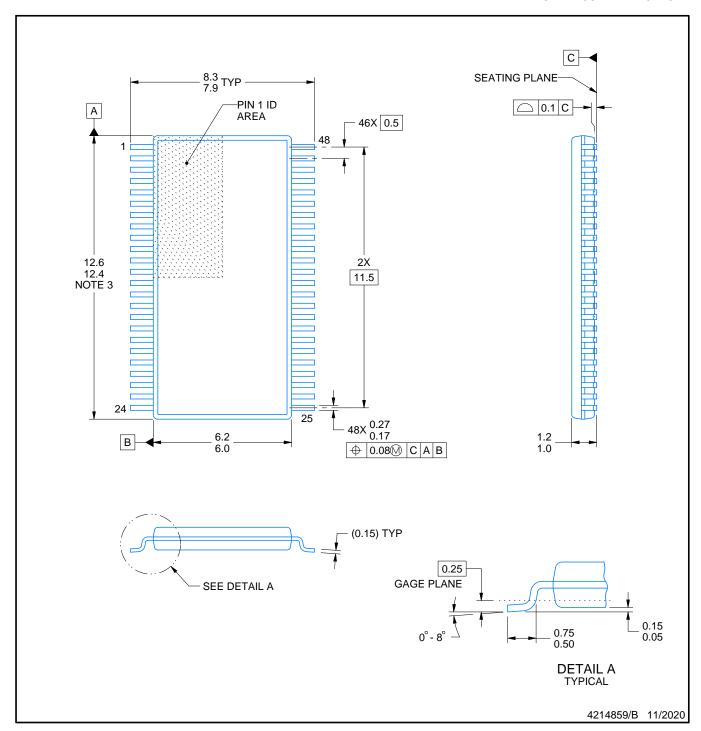
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MO-118

PowerPAD is a trademark of Texas Instruments.





SMALL OUTLINE PACKAGE



NOTES:

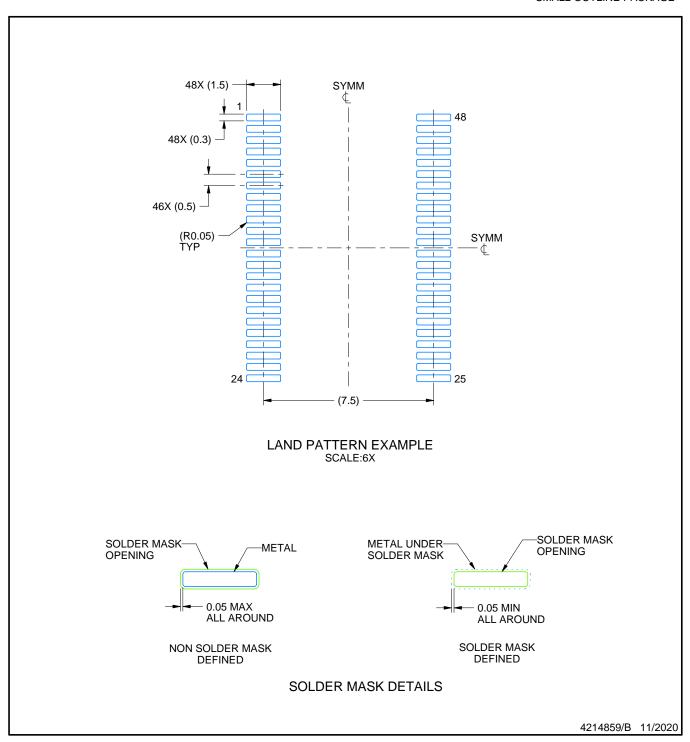
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE

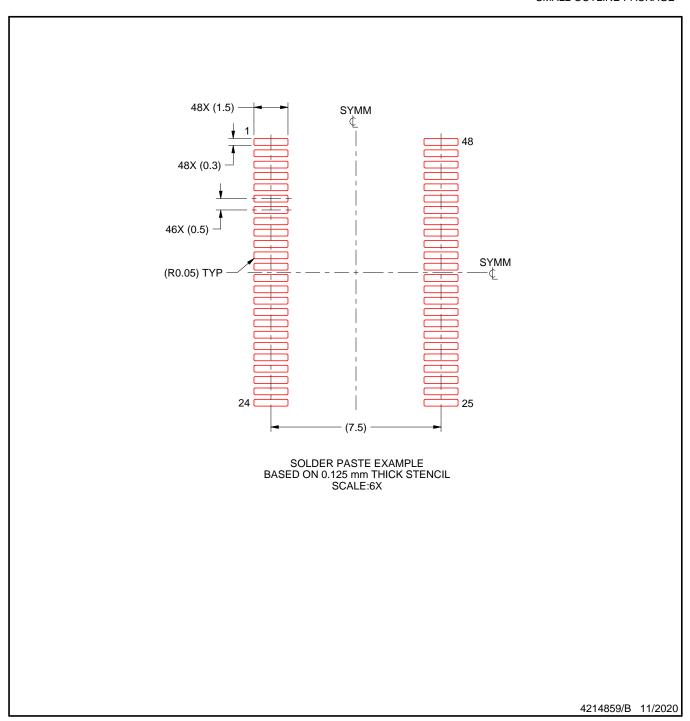


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

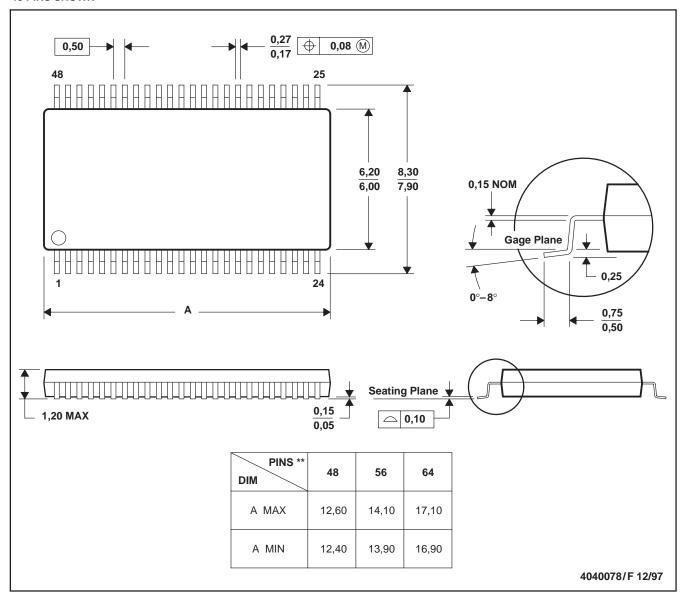
- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025